

100V Single N-Channel HEXFET Power MOSFET in a D2-Pak package; Similar to IRF3710STRL with Lead Free Packaging on Tape and Reel Left

Manufacturers	Infineon Technologies Corporation
Package/Case	TO-263
Product Type	Transistors
RoHS	Green
Lifecycle	



Images are for reference only

Please submit RFQ for IRF3710STRLPBF or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

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Advanced HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

Advanced Process Technology
 Ultra Low On-Resistance
 Dynamic dv/dt Rating
 175°C Operating Temperature
 Fast Switching
 Fully Avalanche Rated

Features

Planar cell structure for wide SOA

Optimized for broadest availability from distribution partners

Product qualification according to JEDEC standard

Silicon optimized for applications switching below <100kHz

Industry standard surface-mount power package

High-current carrying capability package (up to 195 A, die-size dependent)

Capable of being wave-soldered



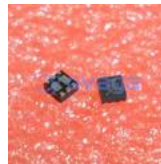


Related Products



[IRLTS6342TRPBF](#)

Infineon Technologies Corporation
TSOP-6



[IRLHS6376TRPBF](#)

Infineon Technologies Corporation
PQFN2x2DD



[IRF9310PBF](#)

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TO-220AB



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SOIC-8